

SEMICONDUCTOR®

November 2013

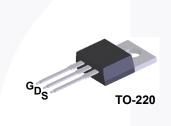
FQP85N06 N-Channel QFET[®] MOSFET 60 V, 85 A, 10 mΩ

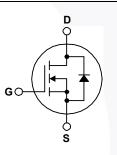
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 85 A, 60 V, $R_{DS(on)}$ = 10 m Ω (Max.) @ V_{GS} = 10 V, I_D = 42.5 A
- Low Gate Charge (Typ. 86 nC)
- Low Crss (Typ. 165 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





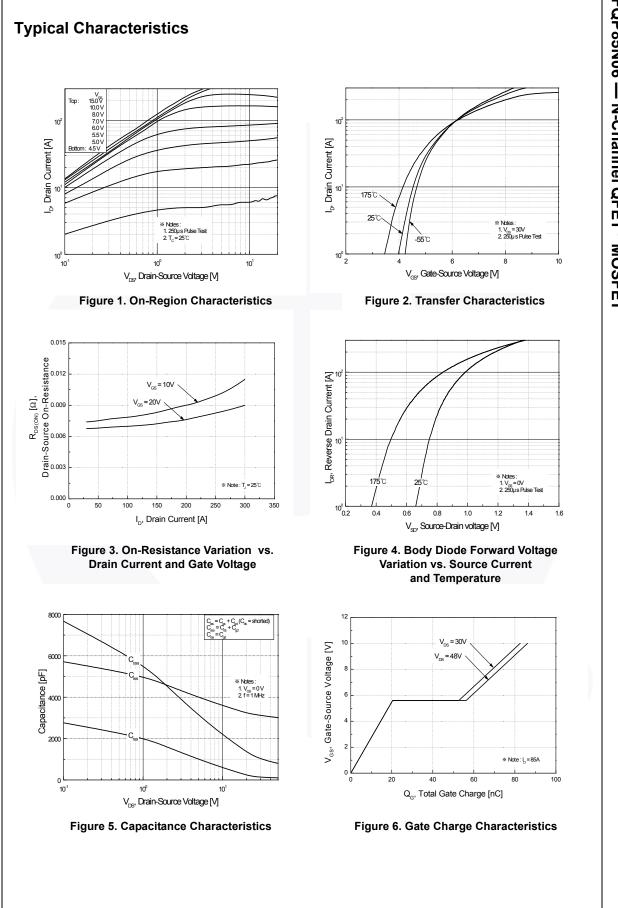
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

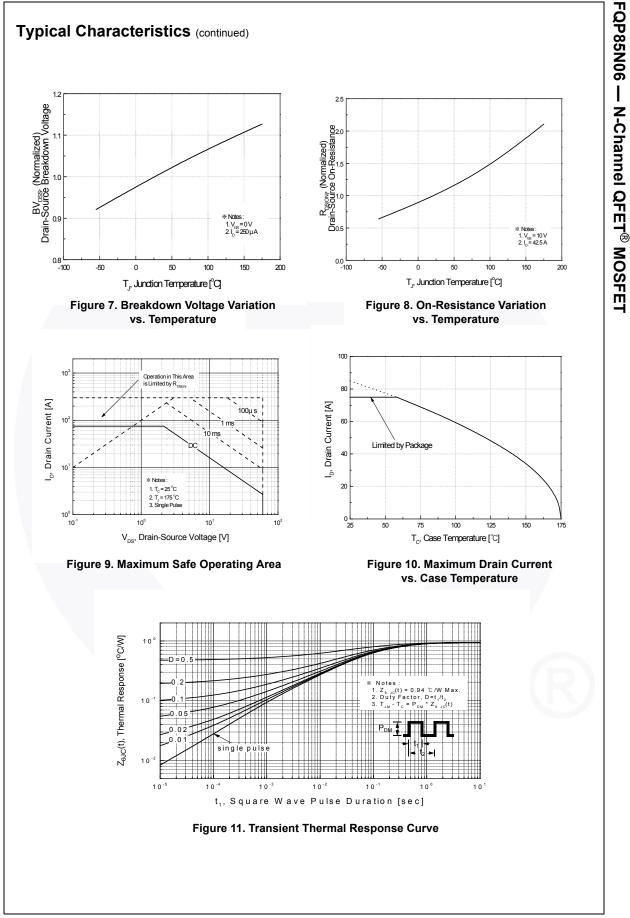
Symbol	Parameter		FQP85N06	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25°C	C) (Note 5)	85	A
	- Continuous (T _C = 100	°C)	60	A
I _{DM}	Drain Current - Pulsed	(Note 1)	300	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	810	mJ
I _{AR}	Avalanche Current	(Note 1)	85	A
E _{AR}	Repetitive Avalanche Energy	(Note 1) 16.0		mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
PD	Power Dissipation ($T_C = 25^{\circ}C$)		160	W
	- Derate above 25°C	1.07	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temperature for Solderin	g,	300	°C
'L	1/8" from Case for 5 seconds		500	C

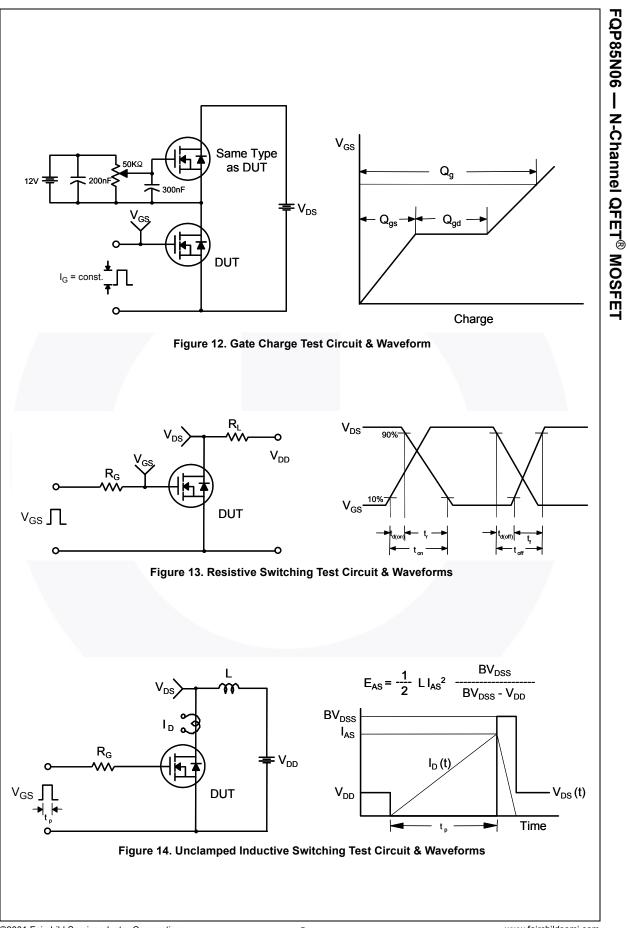
Thermal Characteristics

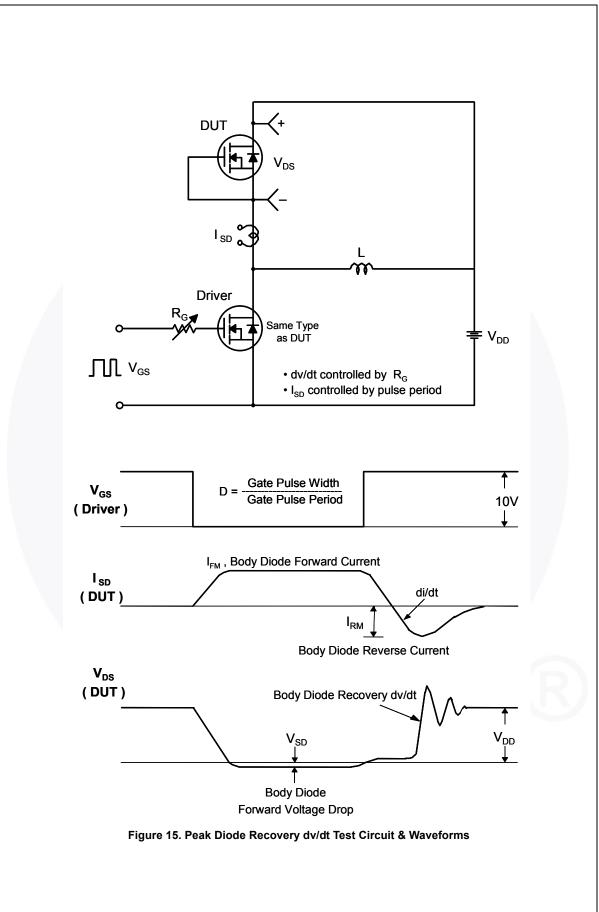
Symbol	Parameter	FQP85N06	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.94	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Part Number Top Mark Package		Package	e Packing Method Ree	Reel Size	Та	Tape Width		Quantity	
FQP85	FQP85N06 FQP85N06 TO-220		Tube N/A		N/A		5	50 units	
lectri	cal Cl	haracteristics	T _C = 25°C	unless otherwise noted.					
Symbol		Parameter		Test Conditi	ons	Min	Тур	Max	Unit
	rootor	viation							
Off Cha ^{3V_{DSS}}			oltogo	V _{GS} = 0 V, I _D = 250 µ	٨	60			V
ABV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = 250 μA		60			V	
ΔT _J	Breakdown Voltage Temperature Coefficient		I_D = 250 µA, Referenced to 25°C			0.06		V/°C	
DSS				V _{DS} = 60 V, V _{GS} = 0 V				1	μA
	Zero Gate Voltage Drain Current		rrent	$V_{DS} = 48 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$				10	μA
GSSF	Gate-E	Body Leakage Curren	t, Forward	V _{GS} = 25 V, V _{DS} = 0 V				100	nA
GSSR		Body Leakage Curren		$V_{GS} = -25 \text{ V}, \text{ V}_{DS} = 0$				-100	nA
On Cha / _{GS(th)}	1	Tistics		V _{DS} = V _{GS} , I _D = 250	uА	2.0		4.0	V
R _{DS(on)}	Static	Drain-Source	-			0.008	0.010	Ω	
	On-Resistance $V_{03} = 25 \text{ V}, I_D = 42.5 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 42.5 \text{ A}$		۰. ۸		54		S		
FS	FUIWa			v _{DS} = 23 v, i _D = 42.0			54		3
Dynam	ic Cha	racteristics							
Siss		Capacitance		V _{DS} = 25 V, V _{GS} = 0 V,			3170	4120	pF
Coss	-	Output Capacitance		f = 1.0 MHz			1150	1500	pF
C _{rss}	Reverse Transfer Capacitance		ice				165	220	pF
Switch	ina Ch	aractariatica							
	· · ·	aracteristics					40	90	ns
d(on) r		On Rise Time		$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 42.5 \text{ A},$ R _G = 25 Ω			230	470	ns
d(off)		Off Delay Time					175	360	ns
d(OIT) f		Off Fall Time			(Note 4)		170	350	ns
ν 2 _g		Bate Charge		V = 40 V I = 05 /			86	112	nC
∽g ⊋ _{gs}		Source Charge		V _{DS} = 48 V, I _D = 85 A, V _{GS} = 10 V (Note 4)			20.5		nC
∽gs ⊋ _{gd}		Drain Charge					36		nC
~gu	Outo 1				(,				
Drain-S				d Maximum Rati	ngs				
s	Maximum Continuous Drain-Source Dic		-Source Dio					85	A
SM		um Pulsed Drain-Sou	1					300	A
/ _{SD}		Source Diode Forwar	d Voltage	,				1.5	V
rr			$V_{GS} = 0 V, I_S = 85 A,$ $dI_F / dt = 100 A/\mu s$			70		ns	
Q _{rr}						135		nC	

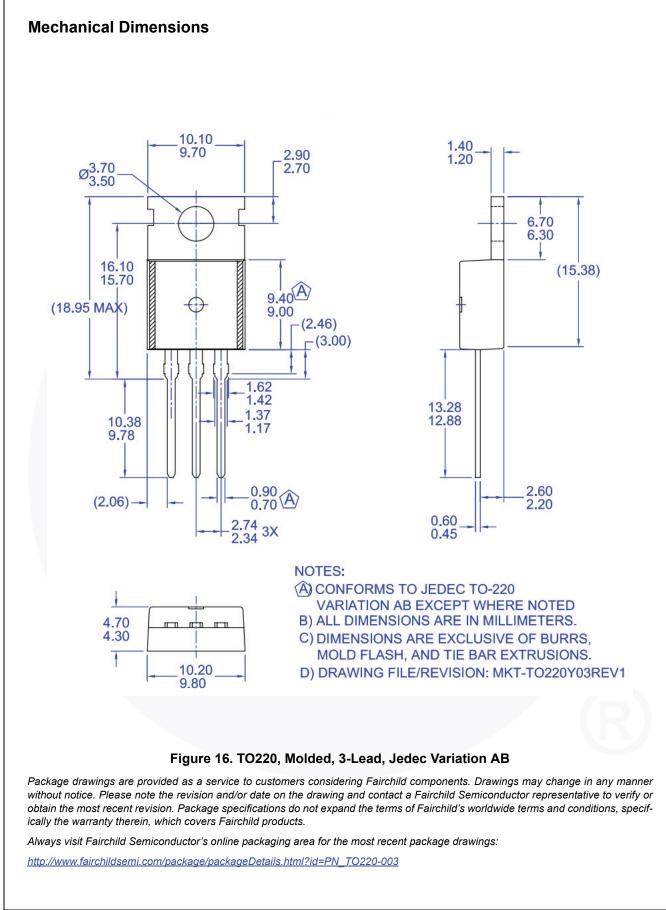








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